		a	DB	Time stamp
L Number	Hits	Search Text (257/207).CCLS.	USPAT;	2002/11/03 12:30
-	333	(257/207).0043.	US-PGPUB	
	143	(257/499).CCLS.	USPAT;	2002/11/03 12:30
-	143	(257/499).0013.	US-PGPUB	
	100	(257/544).CCLS.	USPAT;	2002/11/03 12:31
-	189	(257/544).CCLS.	US-PGPUB	
	718	((257/544) or (257/207) or	EPO; JPO;	2002/11/03 12:31
-	/10	(257/344) OF (257/257) OF (257/499)).CCLS.	DERWENT;	l l
		(237/4337):0000:	IBM TDB	
	1376	((257/207).CCLS.) or ((257/499).CCLS.) or	USPAT;	2002/11/03 12:31
_	13/0	((257/544).CCLS.) or (((257/544) or	US-PGPUB;	1
		(257/207) or (257/499)).CCLS.)	EPO; JPO;	1
		(20172077 02 (2017)	DERWENT;	1
			IBM_TDB	
_	0	(((257/207).CCLS.) or ((257/499).CCLS.) or	USPAT;	2002/11/03 12:32
		((257/544),CCLS.) or (((257/544) or	US-PGPUB;	
		(257/207) or (257/499)).CCLS.)) and strap	EPO; JPO;	
1		adj cell near12 bit adj cell near12	DERWENT;	
		voltage	IBM_TDB	0000/11/03 13:33
_	о	(((257/207).CCLS.) or ((257/499).CCLS.) or	USPAT;	2002/11/03 12:32
1	İ	((257/544).CCLS.) or (((257/544) or	US-PGPUB;	
		(257/207) or (257/499)).CCLS.)) and strap	EPO; JPO;	
		adj cell near12 bit adj cell	DERWENT;	
			IBM_TDB	2002/11/03 12:33
_	0	strap adj cell near12 bit adj cell	USPAT; US-PGPUB;	2002/11/03 12:33
			EPO: JPO:	
			DERWENT;	
	1		IBM TDB	
		-turn and mall	USPAT;	2002/11/03 12:33
_	115	strap adj cell	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	12	(strap adj cell) and 257/\$6.ccls.	USPĀT;	2002/11/03 12:33
	1	(Scrup adj Com, see	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	(11 (02 14 21
_	11	((strap adj cell) and 257/\$6.ccls.) and	USPAT;	2002/11/03 14:31
		(memory adj (device or cell) or sram or	US-PGPUB;	
		rom or eprom or "eprom/flash" or dram)	EPO; JPO; DERWENT;	
			IBM TDB	
		257/96 cole ) and	USPAT;	2002/11/03 12:38
-	0	((strap adj cell) and 257/\$6.ccls.) and (memory adj (device or cell) or sram or	US-PGPUB;	2002, 22, 22
		rom or eprom or "eprom/flash" or dram) and	EPO; JPO;	
		bit adj cell and strap adj cell	DERWENT;	
	1	Die auf Cell and Belap auf Soll	IBM TDB	
l	4	((strap adj cell) and 257/\$6.ccls.) and	USPAT;	2002/11/03 12:45
_	]	(memory adj (device or cell) or sram or	US-PGPUB;	
		rom or eprom or "eprom/flash" or dram) and	EPO; JPO;	
		bit adj (line or cell) and strap adj cell	DERWENT;	
			IBM_TDB	0000/11/00 10 10
_	0	((strap adj cell) and 257/\$6.ccls.) and	USPAT;	2002/11/03 12:40
		(memory adi (device or cell) or sram or	US-PGPUB;	
		rom or eprom or "eprom/flash" or dram) and	EPO; JPO;	
		bit adj (line or cell) and strap adj cell	DERWENT; IBM TDB	
	1	and voltage near12 body near12 strap	USPAT;	2002/11/03 12:40
-	0	((strap adj cell) and 257/\$6.ccls.) and (memory adj (device or cell) or sram or	US-PGPUB;	
}		(memory adj (device or cell) of slam of rom or eprom or "eprom/flash" or dram) and		
	1	bit adj (line or cell) and strap adj cell	DERWENT;	
-		and voltage near15 body near15 strap	IBM TDB	
4	1	((strap adj cell) and 257/\$6.ccls.) and	USPAT;	2002/11/03 12:41
-		(memory adi (device or cell) or sram or	US-PGPUB;	
Ì		rom or eprom or "eprom/flash" or dram) and	EPO; JPO;	
		bit adj (line or cell) and strap adj cell	DERWENT;	
		and voltage near12 strap	IBM TDB	

	1	((strap adj cell) and 257/\$6.ccls.) and	USPAT;	2002/11/03 12:45
		(memory adi (device or cell) or sram or	US-PGPUB;	
	]	rom or eprom or "eprom/flash" or dram) and	EPO; JPO; DERWENT;	
		bit adj (line or cell) and strap adj cell	IBM TDB	
		and voltage near12 supply	USPĀT	2002/11/03 12:56
-	4	(US-RE36837-\$ or US-6150686-\$ or US-5616961-\$ or US-5369049-\$).did.	OSIAI	2002, 21, 00 1110
		body nearl2 strap adj cell nearl2 (voltage	USPAT;	2002/11/03 12:57
-	) 0	or potential or bias or biased)	US-PGPUB;	
1		or potential of bias of biases,	EPO; JPO;	
	1		DERWENT;	
			IBM TDB	
	1	strap adj cell near12 (voltage or	USPĀT;	2002/11/03 14:02
-		potential or bias or biased)	US-PGPUB;	
		F-1	EPO; JPO;	1
			DERWENT;	
1			IBM_TDB	0000 (11 (00 14:00
	0	("999361.ap.").PN.	USPAT;	2002/11/03 14:02
Ì			US-PGPUB;	ļ
	1		EPO; JPO; DERWENT;	
			IBM TDB	
1		000061	USPAT;	2002/11/03 14:02
-	3	999361.ap.	US-PGPUB;	2002, 22, 00
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
	0	buried adj strap adj cell near12 bias	USPAT;	2002/11/03 14:32
			US-PGPUB;	İ
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/11/02 14:33
_	146	(best or buried adj strap adj cell) near12	USPAT;	2002/11/03 14:33
ł		(bias or voltage or body or offset) near12	US-PGPUB; EPO; JPO;	
		bit	DERWENT;	
			IBM TDB	
1		(best or buried adj strap adj cell) near12	USPAT;	2002/11/03 14:34
-	0	(bias or voltage or body or offset) near12	US-PGPUB;	
		bit adj cell	EPO; JPO;	
1		bit day coll	DERWENT;	
			IBM_TDB	
_	4	(best or buried adj strap adj cell) near12	USPAT;	2002/11/03 14:36
		(bias or voltage or body or offset) near12	US-PGPUB;	ļ
		bit adj (cell or line)	EPO; JPO; DERWENT;	
			IBM TDB	
		(buried adj strap adj cell) near12 (bias	USPAT;	2002/11/03 14:46
-	0	or voltage or body or offset) near12 bit	US-PGPUB;	
		adj (cell or line)	EPO; JPO;	
	1	44, (5522 52 2207)	DERWENT;	
			IBM_TDB	
-	0	(buried adj strap) near12 (bias or voltage	USPAT;	2002/11/03 14:39
		or body or offset) near12 bit adj (cell or	US-PGPUB;	
		line)	EPO; JPO;	
			DERWENT; IBM TDB	
	_	de la company de	USPAT;	2002/11/03 14:41
-	0	strap adj (line or cell or row or column) near12 (bias or voltage or body or offset)	US-PGPUB;	
		near12 (blas of voltage of body of offset) near12 bit adj (cell or line or row or	EPO; JPO;	
1	1	column)	DERWENT;	
			IBM_TDB	
_	0	strap adj (line or cell or row or column)	USPAT;	2002/11/03 14:42
		near12 (bias or voltage or body or offset	US-PGPUB;	
1		or potential) near12 bit adj (cell or line	EPO; JPO;	
	1	or row or column)	DERWENT;	
Ī			IBM TDB	<u> </u>

			UCDAM.	2002/11/03 14:42
-	1	strap near12 (bias or voltage or body or	USPAT; US-PGPUB;	2002/11/03 14.42
		offset or potential) nearly bit adj (cell	EPO; JPO;	
		or line or row or column)	DERWENT;	
			IBM TDB	i
		(buried adj strap adj cell) near12 bit adj	USPAT;	2002/11/03 14:46
-	0	(buried adj strap adj cell) healtz bit adj	US-PGPUB;	
ł		(cell or line)	EPO; JPO;	
			DERWENT;	
1	İ		IBM TDB	
	1.0	buried adj strap near12 bit adj (cell or	USPĀT;	2002/11/03 14:56
-	16	line)	US-PGPUB;	
		( line)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
	1	buried adj strap near12 bit adj (cell or	USPĀT;	2002/11/03 14:51
-	1	line) and strap adj (line or cell)	US-PGPUB;	}
		Time, and secup and version	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	7	(US-6150686-\$ or US-RE36837-\$ or	USPAT;	2002/12/01 17:23
1		US-4724190-\$ or US-6455886-\$ or	US-PGPUB	
		US-5616961-\$ or US-5369049-\$).did. or		
1		(US-20020080676-\$).did.		2002/12/01 17:25
_	0	bit add line and word add line and dummy	USPAT;	2002/12/01 17:25
1		adj cell and body near12 (potential or	US-PGPUB;	
	ļ	voltage) and sram.ti,ab,clm. and	EPO; JPO;	1
		leakage.ti,ab,clm.	DERWENT;	
			IBM_TDB	2002/12/01 17:25
_	895	bit adj line and word adj line and dummy	USPAT;	2002/12/01 17.25
		adj cell	US-PGPUB;	
Ì			EPO; JPO;	1
			DERWENT;	
		and the second disperse	IBM_TDB USPAT;	2002/12/01 18:25
-	7	bit adj line and word adj line and dummy	US-PGPUB;	2002/12/01 10:20
		adj cell near12 body and (leakage or	EPO; JPO;	
		leaking or leak)	DERWENT;	
			IBM TDB	
	15.61	((257/204) or (257/205) or (257/206) or	USPAT;	2002/12/01 18:25
<del>-</del>	1561	((257/204) of (257/203) of (257/200) of (257/200)	US-PGPUB;	
		(257/2077).0015.	EPO; JPO;	
			DERWENT;	
j			IBM TDB	1
1_	Α.	(((257/204) or (257/205) or (257/206) or	USPĀT;	2002/12/01 18:55
\ _	]	((257/207)).CCLS.) and (bit-line or bit adj	US-PGPUB;	
		line or bitline) near12 dummy	EPO; JPO;	
		•	DERWENT;	
			IBM_TDB	0000/10/01 10:30
_	1	(((257/204) or (257/205) or (257/206) or	USPAT;	2002/12/01 19:30
		(257/207)).CCLS.) and (strap adj cell or	US-PGPUB;	
		dummy adj cell) and gate adj array	EPO; JPO;	
	Ì		DERWENT;	
		1057 (000)	IBM_TDB USPAT;	2002/12/01 19:35
-	2	(((257/204) or (257/205) or (257/206) or	USPAT; US-PGPUB;	2002/12/01 19.33
		(257/207)).CCLS.) and (strap adj cell or	EPO; JPO;	
		dummy adj cell) and (leakage or leaking or	DERWENT;	
1		leak)	IBM TDB	
		de la colla participa de colla p	USPAT;	2002/12/01 19:36
-	1 15	(strap adj cell or dummy adj cell) near15 body and (leakage or leaking or leak)	US-PGPUB;	
		pody and (leakage of leaking of leak)	EPO; JPO;	
			DERWENT;	
ĺ			IBM TDB	
	0.0	(body adj bias or body adj strap or body	USPAT;	2002/12/11 09:33
-	9	adj contact) and memory.ti,ab,clm. and	US-PGPUB;	
		257/\$6.ccls.	EPO; JPO;	
		20.740.0020	DERWENT;	
			IBM TDB	

				2002/12/11 09:34
-	73	(body adj bias or body adj strap or body adj contact) and memory.ti,ab,clm. and 257/\$6.ccls. and (bit adj line or bitline or bit-line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/11 09:34
-	21	(body adj bias or body adj strap or body adj contact) same (bitline or bit-line or bit adj line) and memory.ti,ab,clm. and	USPĀT; US-PGPUB	2002/12/11 09:36
_	0	257/\$6.ccls. (body adj bias or body adj strap or body adj contact) near15 (bitline or bit-line or bit adj line) and memory.ti,ab,clm. and	EPO; JPO; DERWENT; IBM_TDB	2002/12/11 09:36
-	1	257/\$6.ccls. (body adj bias or body adj strap or body adj contact) near15 (bitline or bit-line or bit adj line) and memory.ti,ab,clm.	EPO; JPO; DERWENT; IBM TDB	2002/12/11 09:37
-	1	((body adj bias or body adj strap or body adj contact) same (bitline or bit-line or bit adj line) and memory.ti,ab,clm. and 257/\$6.ccls.) or ((body adj bias or body adj strap or body adj contact) near15 (bitline or bit-line or bit adj line) and	EPO; JPO; DERWENT; IBM_TDB	2002/12/11 09:37
-	22	memory.ti,ab,clm.) ((body adj bias or body adj strap or body adj contact) same (bitline or bit-line or bit adj line) and memory.ti,ab,clm. and 257/\$6.ccls.) or ((body adj bias or body adj strap or body adj contact) near15 (bitline or bit-line or bit adj line) and memory.ti,ab,clm.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 10:45
_	2	("6018172").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 09:56
-	0	(((body adj bias or body adj strap or body adj contact) same (bitline or bit-line or bit adj line) and memory.ti,ab,clm. and 257/\$6.ccls.) or ((body adj bias or body adj strap or body adj contact) near15 (bitline or bit-line or bit adj line) and memory.ti,ab,clm.)) and leakage.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 10:46
_	14	(((body adj bias or body adj strap or body adj contact) same (bitline or bit-line or bit adj line) and memory.ti,ab,clm. and 257/\$6.ccls.) or ((body adj bias or body adj strap or body adj contact) near15 (bitline or bit-line or bit adj line) and memory.ti,ab,clm.)) and leakage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 10:46
-	8	(((body adj bias or body adj strap or body adj contact) same (bitline or bit-line or bit adj line) and memory.ti,ab,clm. and 257/\$6.ccls.) or ((body adj bias or body adj strap or body adj contact) near15 (bitline or bit-line or bit adj line) and memory.ti,ab,clm.)) and leakage adj	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 15:14
-	15	current (((body adj bias or body adj strap or body adj contact) same (bitline or bit-line or bit adj line) and memory.ti,ab,clm. and 257/\$6.ccls.) or ((body adj bias or body adj strap or body adj contact) near15 (bitline or bit-line or bit adj line) and memory.ti,ab,clm.)) and leakage adj current and cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 15:44

			иораш.	2002/12/11 15:36
<del></del>	0 [	(((body adj bias or body adj strap or body	USPAT; US-PGPUB;	2002/12/11 13:30
	-	add contact) same (bitline or bit-line or		
		hit add line) and memory.tl,ab,cim. and	EPO; JPO; DERWENT;	
i		257/66 ccls.) or ((body ad) blas or body		
		adi strap or body adi contact) neario	IBM_TDB	
		(bitline or bit-line or bit ad) line) and		
	1	memory.ti.ab.clm.)) and leakage adj		
1		current and cmos.ti.ab.clm.		0000/10/11 16:59
	1	thody add bias or body add strap or body	USPAT;	2002/12/11 16:58
-	1	adi contact) same (bitline or bit-line or	US-PGPUB;	
		bit add line) and memory.tl,ab,clm. and	EPO; JPO;	
		(365/\$6.ccls. or 257/\$6.ccls.) and leakage	DERWENT;	
1		adj current and cmos.ti,ab,clm.	IBM_TDB	
		(cmos or cmosfet).ti,ab,clm. and (body adj	USPĀT;	2002/12/11 17:02
-	1	contact or body adj strap or body adj	US-PGPUB;	
		bias) near12 (seperate or each or both)	EPO; JPO;	
		near12 (NMOS or PMOS or n-channel or	DERWENT;	
		p-channel or NMOSFET or PMOSFET)	IBM TDB	
	ļ	p-channel or NMOSFEL of PMOSFEL)	USPAT;	2002/12/11 17:05
i <b>-</b>	1	(cmos or cmosfet).ti,ab,clm. and (body adj	US-PGPUB;	
		contact or body adj strap or body adj	EPO; JPO;	
		bias) near12 (separate or each or both)	DERWENT;	
		near12 (NMOS or PMOS or n-channel or	IBM TDB	
}	İ	p-channel or NMOSFET or PMOSFET)	USPAT;	2002/12/11 17:17
-	10	(cmos or cmosfet) and (body adj contact or	US-PGPUB;	2002, 22, 2
1	1	body adj strap or body adj bias) near12	EPO; JPO;	1
	Į	(separate or each or both) near12 (NMOS or	DERWENT;	1
		PMOS or n-channel or p-channel or NMOSFET		
		or PMOSFET)	IBM_TDB	2002/12/11 18:28
<u>-</u>	49	(cmos or cmosfet) and (body adj contact or	USPAT;	2002/12/11 10.20
		hody add strap or body add bias or body	US-PGPUB;	1
	ļ	add fixing or body add potential) same	EPO; JPO;	
		(separate or each or both) same (NMOS or	DERWENT;	
		PMOS or n-channel or p-channel or NMOSFET	IBM_TDB	
	1	or PMOSFET)		
	19		USPAT;	2002/12/11 18:34
_	1	hody add strap or body add bias or body	US-PGPUB;	
		adj fixing or body adj potential) same	EPO; JPO;	
		(separate or each or both) same (NMOS or	DERWENT;	}
Ì		PMOS or n-channel or p-channel or NMOSFET	IBM_TDB	
	1	or PMOSFET) same leakage	_	
	1	(cmos or cmosfet) and (body adj node or	USPAT;	2002/12/11 18:35
-	20	body adj contact or body adj strap or body	US-PGPUB	
		adj bias or body adj fixing or body adj		1
		potential) same (separate or each or both)		
		same (NMOS or PMOS or n-channel or		
1		same (NMUS OF PMUS OF IN-CHARMET OF		
		p-channel or NMOSFET or PMOSFET) same		1
	1	leakage		